

## TSM1NB60SCT B0G

#### **TSM1NB60SCT B0G Information**

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For Reference Only

Part Number TSM1NB60SCT B0G Manufacturer TSC America Inc.

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET, SINGLE, N-CHANNEL, PLANA

Package TO-226-3, TO-92-3 (TO-226AA)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## **TSM1NB60SCT B0G Specifications**

Manufacturer Part Number         TSMINB60SCT B0G           Manufacturer         TSC America Inc.           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-226-3, TO-92-3 (TO-226AA)           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         500mA (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4.5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         6.1nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         138pF @ 25V           Vgs (Max)         ±39 V           FET Feature         -           Power Dissipation (Max)         2.5W (Tc)           Rds On (Max) @ Id, Vgs         10 Ohm @ 250mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-92           Package / Case         TO-226-3, TO-92-3 (TO-226AA)		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-226-3, TO-92-3 (TO-226AA)           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         500mA (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4.5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         6.1nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         138pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         2.5W (Tc)           Rds On (Max) @ Id, Vgs         10 Ohm @ 250mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-92           Package / Case         TO-226-3, TO-92-3 (TO-226AA)	Manufacturer Part Number	TSM1NB60SCT B0G
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FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  600V  Current - Continuous Drain (Id) @ 25°C  500mA (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  10 Ohm @ 250mA, 10V  Perating Temperature  Mounting Type  Supplier Device Package  Package / Case  N-Channel  MOSFET (Metal Oxide)  MOSFET (Metal Oxide)  MOSFET (Metal Oxide)  600V  600	Package	TO-226-3, TO-92-3 (TO-226AA)
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C500mA (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 250μAGate Charge (Qg) (Max) @ Vgs6.1nC @ 10VInput Capacitance (Ciss) (Max) @ Vds138pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Tc)Rds On (Max) @ Id, Vgs10 Ohm @ 250mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92Package / CaseTO-226-3, TO-92-3 (TO-226AA)	Series	-
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Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  4.5V @ 250μA  Gate Charge (Qg) (Max) @ Vgs  6.1nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  138pF @ 25V  Vgs (Max)  ±30V  FET Feature  - Power Dissipation (Max)  2.5W (Tc)  Rds On (Max) @ Id, Vgs  10 Ohm @ 250mA, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-92  Package / Case  TO-226-3, TO-92-3 (TO-226AA)	Drain to Source Voltage (Vdss)	600V
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Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  10 Ohm @ 250mA, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-92  Package / Case  TO-226-3, TO-92-3 (TO-226AA)	Vgs(th) (Max) @ Id	4.5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Tc)Rds On (Max) @ Id, Vgs10 Ohm @ 250mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92Package / CaseTO-226-3, TO-92-3 (TO-226AA)	Gate Charge (Qg) (Max) @ Vgs	6.1nC @ 10V
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Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  10 Ohm @ 250mA, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-92  Package / Case  TO-226-3, TO-92-3 (TO-226AA)	Vgs (Max)	±30V
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Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-92  Package / Case  TO-226-3, TO-92-3 (TO-226AA)	Power Dissipation (Max)	2.5W (Tc)
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Supplier Device Package TO-92 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-226-3, TO-92-3 (TO-226AA)	Mounting Type	Through Hole
	Supplier Device Package	TO-92
Report errors?	Package / Case	TO-226-3, TO-92-3 (TO-226AA)
		Report errors?

#### **TSM1NB60SCT B0G Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **TSM1NB60SCT B0G Payment Methods**



















# TSM1NB60SCT B0G Shipping Methods













If you have any question about TSM1NB60SCT B0G, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com